## Thyristor High Voltage, Phase Control SCR, 80 A



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PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub>	80 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V						
V <sub>TM</sub> (typ.)	1.16 V						
I <sub>GT</sub>	100 mA						
TJ	-40 °C to +150 °C						
Package	TO-247AD 3L						
Circuit configuration	Single SCR						

### **FEATURES**

- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- 150 °C maximum operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **APPLICATIONS**

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

### DESCRIPTION

The VS-80TPS16L high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V					
On-state voltage	V <sub>T</sub>	80 A, T <sub>J</sub> = 125 °C, typical	1.16	v					
Average rectified forward current	I <sub>T(AV)</sub>		80						
Maximum continuous RMS on-state current	I <sub>RMS</sub>		126	А					
Non-repetitive peak surge current	I <sub>TSM</sub>		1000						
Maximum rate of rise	dV/dt		1000	V/µs					
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +150	°C					

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	TYP. I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-80TPS16L-M3	1600	1700	10					

COMPLIANT HALOGEN FREE

RoHS

# VS-80TPS16L-M3



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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL	TEST CONDITIONS			MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	$T_{C}$ = 113 °C, 180° conduction half sine v	-	80		
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>		-	126	А	
Peak, one-cycle non-repetitive surge current	<b></b>	10 ms sine pulse, rated $V_{\text{RRM}}$ applied		-	840	
reak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	Initial T <sub>J</sub> =	-	1000	
12t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{\text{RRM}}$ applied	T <sub>J</sub> maximum	-	3536	A20
I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no voltage reapplied		-	5000	A <sup>2</sup> s
$I^2 \sqrt{t}$ for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	d, T <sub>J</sub> = 125 °C	-	50 000	A²√s
		80 A, T <sub>J</sub> = 25 °C		1.22	1.40	
On-state voltage	V <sub>T</sub>	160 A, T <sub>J</sub> = 25 °C		1.48	1.66	v
		80 A, T <sub>J</sub> = 125 °C		1.16	1.24	
		160 A, T <sub>J</sub> = 125 °C			1.62	
Low level value of threshold voltage	V <sub>T01</sub>	T 450.00		-	0.80	N/
High level value of threshold voltage	V <sub>T02</sub>	T <sub>J</sub> = 150 °C		-	0.89	V
Low level value of on-state slope resistance	r <sub>t1</sub>	T 450.00		-	4.82	
High level value of on-state slope resistance	r <sub>t2</sub>	T <sub>J</sub> = 150 °C		-	4.51	mΩ
Rate of rise of turned-on current	dl/dt	$T_{J}$ = 125 °C, $V_{R}$ = 1000 V, $I_{T}$ = 100 A, $I_{gt}$ $V_{GT}$ = 2.5 V	= 450 mA,	-	500	A∕µs
Holding current	Ι <sub>Η</sub>			-	200	
Latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		-	400	mA
	1 /1	T <sub>J</sub> = 25 °C		50	200	μA
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 125 °C		10	60	mA
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V <sub>DRM</sub> , I	R <sub>g</sub> -k = open	-	1000	V/µs

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Peak gate power	P <sub>GM</sub>	10 ms sino pul	so no voltago rospoliod	-	10	w
Average gate power	P <sub>G(AV)</sub>		10 ms sine pulse, no voltage reapplied			
Peak gate current	I <sub>GM</sub>				2.5	А
Peak negative gate voltage	-V <sub>GM</sub>					v
Required DC gate voltage to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	-	1.5	v
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	-	100	mA
DC gate voltage not to trigger	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DBM</sub> = 80 % rated value		-	0.20	V
DC gate current not to trigger	I <sub>GD</sub>	$i_{\rm J} = 125$ C, V	DRM = 00 % rated value	-	5	mA

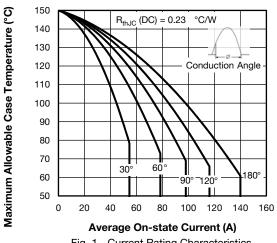
SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t <sub>gt</sub>	$I_T$ = 80 A, $V_D$ = 50 $\%$ $V_{DRM},$ $I_{gt}$ = 300 mA, $T_J$ = 25 $^\circ C$	2	-	
Turn-off time	tq	$\label{eq:IT} \begin{array}{l} I_T = 80 \text{ A}, \text{ V}_D = 80 \ \% \ \text{V}_{DRM}, \ \text{dV/dt} = 20 \ \text{V/}\mu\text{s}, \ t_p = 200 \ \mu\text{s} \\ I_{gt} = 100 \ \text{mA}, \ \text{dI/dt} = 10 \ \text{A/}\mu\text{s}, \ \text{V}_R = 100 \ \text{V}, \ \text{T}_J = 150 \ ^\circ\text{C} \end{array}$	150	-	μs

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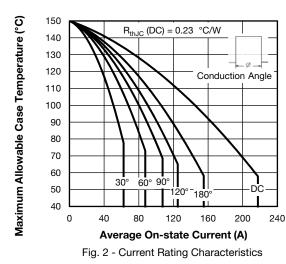


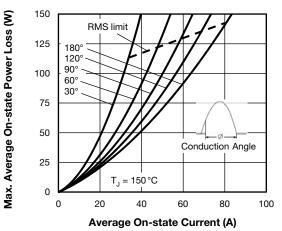
THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	MAX.	UNITS			
Maximum operating junction and storage temperature range		TJ, T <sub>Stg</sub>		-40	150	°C			
Maximum thermal resistance, junction to c	R <sub>thJC</sub>		-	0.23					
Maximum thermal resistance, junction to a	R <sub>thJA</sub>		-	40	°C/W				
Typical thermal resistance, case to heatsin	k	R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.	20				
Approximate weight				6 (0	.21)	g (oz.)			
Mounting torgue	minimum			6	(5)	kgf ⋅ cm			
	maximum			12	(10)	(lbf ⋅ in)			
Marking device			Case style TO-247AD 3L		80TPS1	6L			

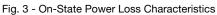
SINE HALF-WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION					UNITS	
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-80TPS16L-M3	0.031	0.036	0.040	0.042	0.044	0.028	0.036	0.038	0.040	0.042	°C/W











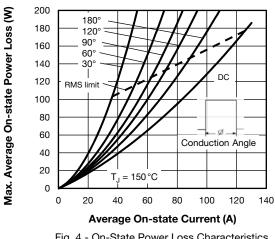


Fig. 4 - On-State Power Loss Characteristics

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3

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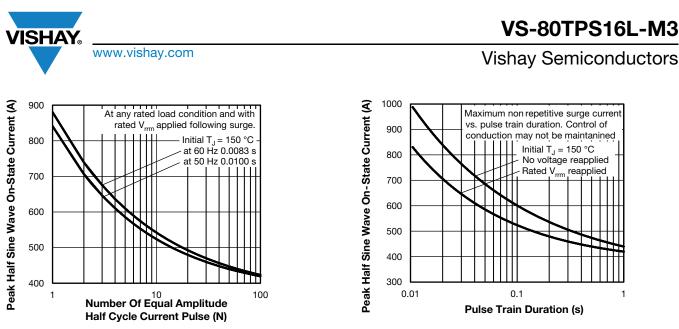


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current

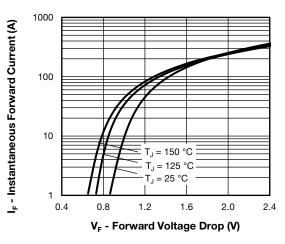
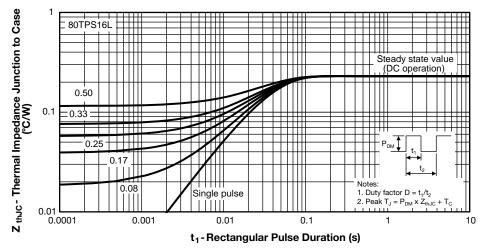


Fig. 7 - On-State Voltage Drop Characteristics







### **ORDERING INFORMATION TABLE**

Device code	VS-	80	т	Р	S	16	L	-M3
	1	2	3	4	5	6	7	8
	2	- Cur - Circ	hay Sen rent coc cuit conf	le (80 = iguratio	80 A)	oduct		
	4 5	• P=	thyristo TO-247 e of silio	' packaç	je			
	7	- Voli - Pac	standar tage coo kage L 3 = halog	de (16 = = long le	1600 V ead	)	ant, and	l termina

ORDERING INFORMATION (example)							
PREFERRED P/N         QUANTITY PER TUBE         MINIMUM ORDER QUANTITY         PACKAGING DESCRIPTION							
VS-80TPS16L-M3	25	500	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95626				
Part marking information	www.vishay.com/doc?95007				



TO-247AD 3L

### **DIMENSIONS** in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØК	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- <sup>(3)</sup> Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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